

Conjugated polyelectrolytes for stable perovskite solar cells based on methylammonium lead triiodide

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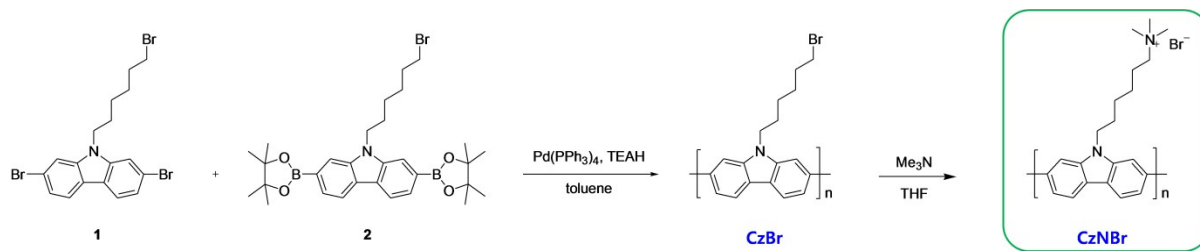


Fig. S1 - Synthetic route of CzNBr.

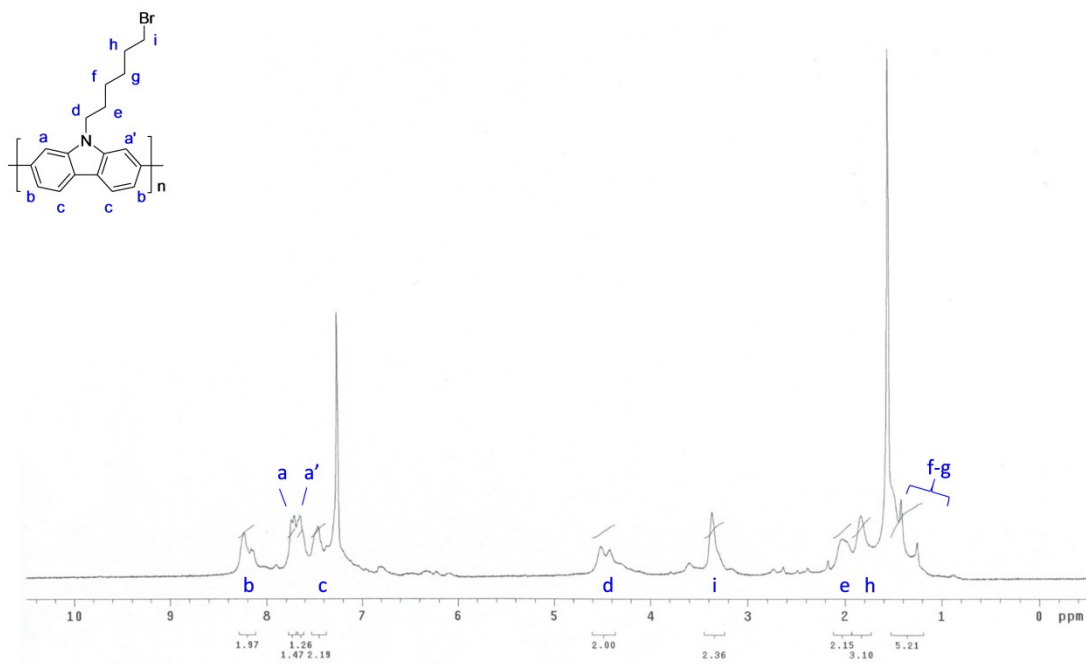


Fig. S2 - ¹H NMR of CzB.

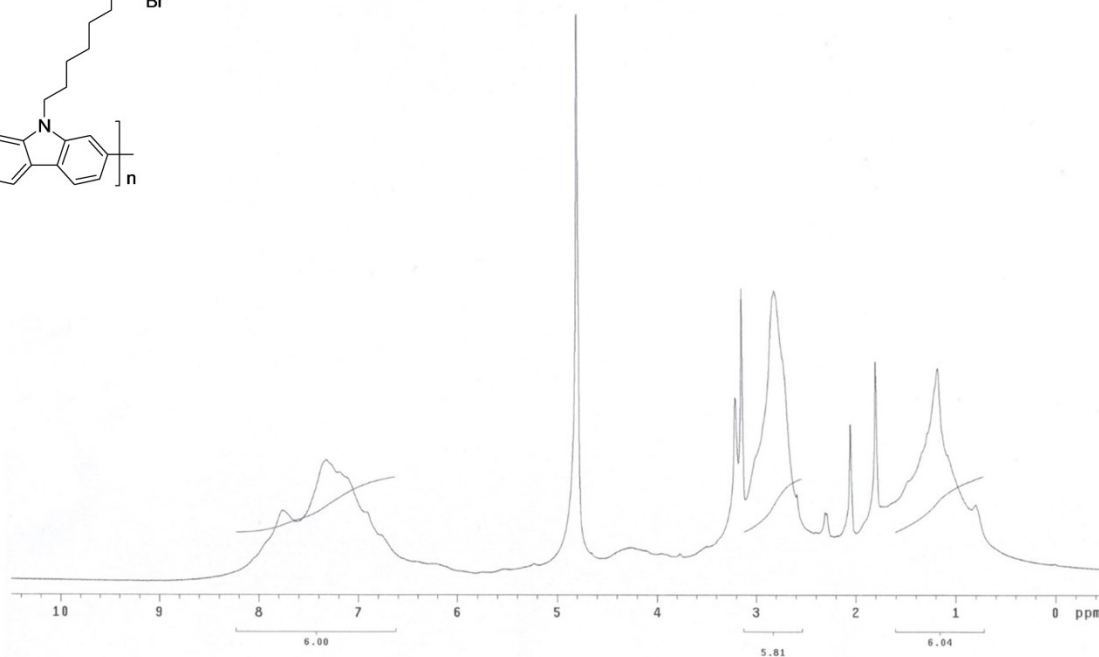
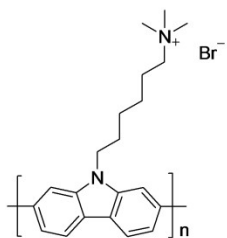


Fig. S3 - ¹H NMR of CzNBr.

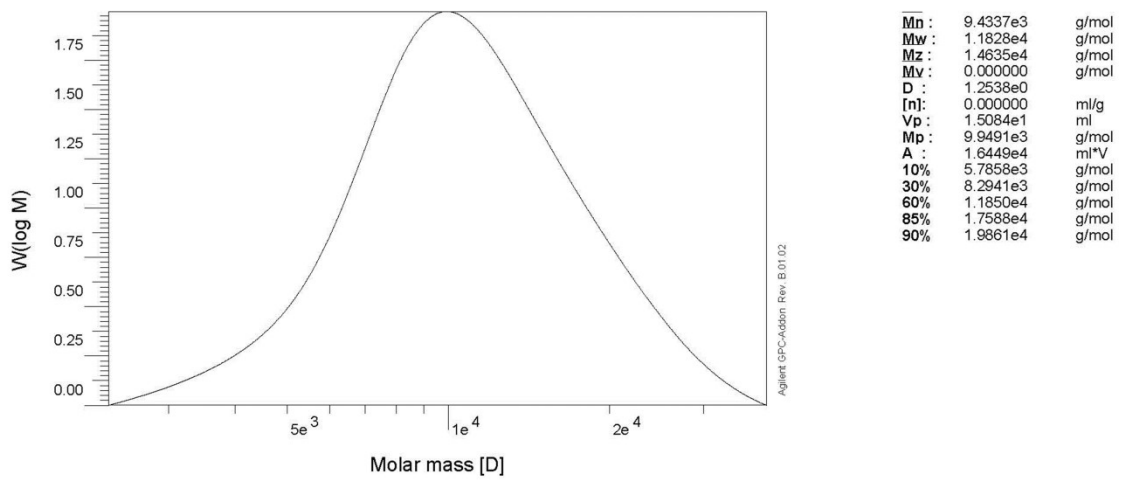
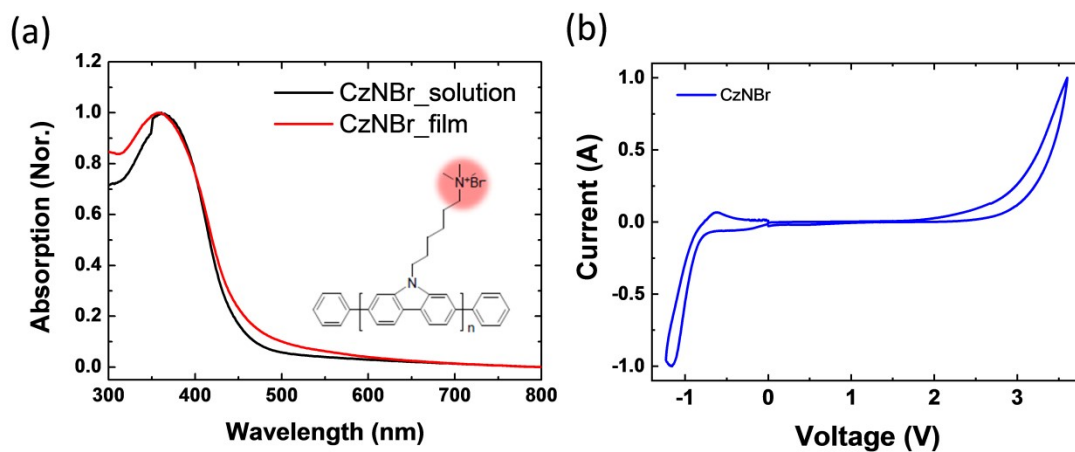


Fig. S4 - Gel Permeation Chromatography (GPC) data of CzNBr.



	$\lambda_{\text{max-solution}}^{\text{a}}(\text{nm})$	$\lambda_{\text{max-film}}(\text{nm})^{\text{a}}$	$E_g^{\text{opt}}(\text{eV})^{\text{b}}$	HOMO (eV)	LUMO (eV)	$E_g^{\text{ele}}(\text{eV})$
CzNBr	363	360	2.74	-6.79	-3.95	2.84

* $E_{\text{HOMO}} = -([\text{E}_{\text{onset}}]_{\text{ox}} + 4.8) \text{ eV}$, $E_{\text{LUMO}} = -([\text{E}_{\text{onset}}]_{\text{red}} + 4.8) \text{ eV}$

Fig. S5 - Optical and electrochemical characteristics of CzNBr in solution and film.

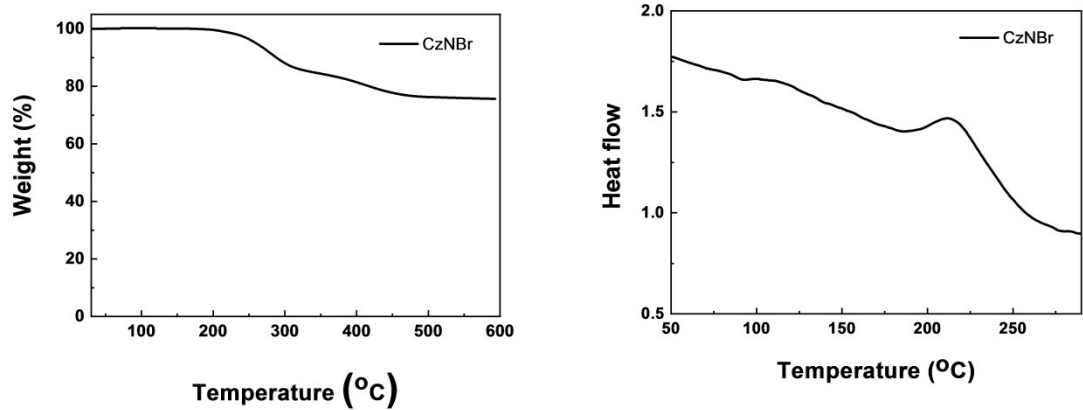


Fig. S6 - Thermogravimetric analysis (TGA) of CzNBr under N₂ conditions.

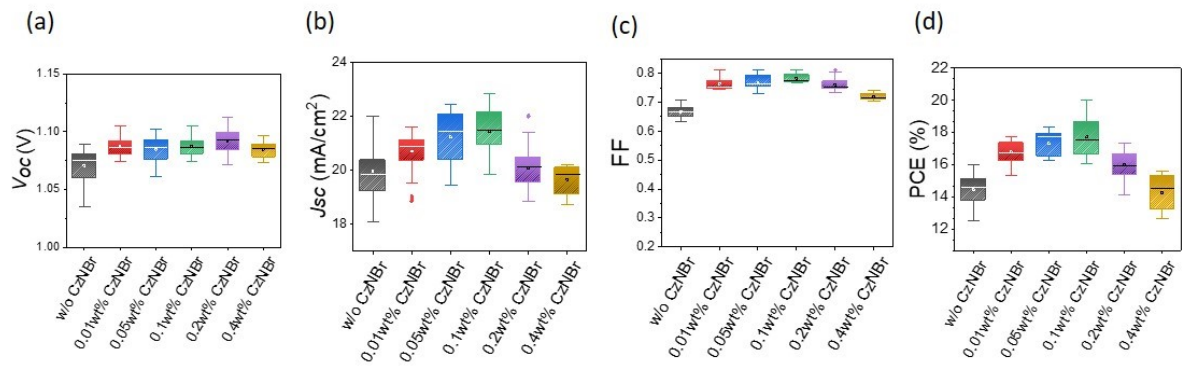


Fig. S7 - Statics of the device parameters depending on various concentrations of CzNBr solution from 0 to 0.4 wt%. (a) The V_{oc} , (b) J_{sc} , (c) FF and (d) PCE were calibrated for 30 devices for each condition.

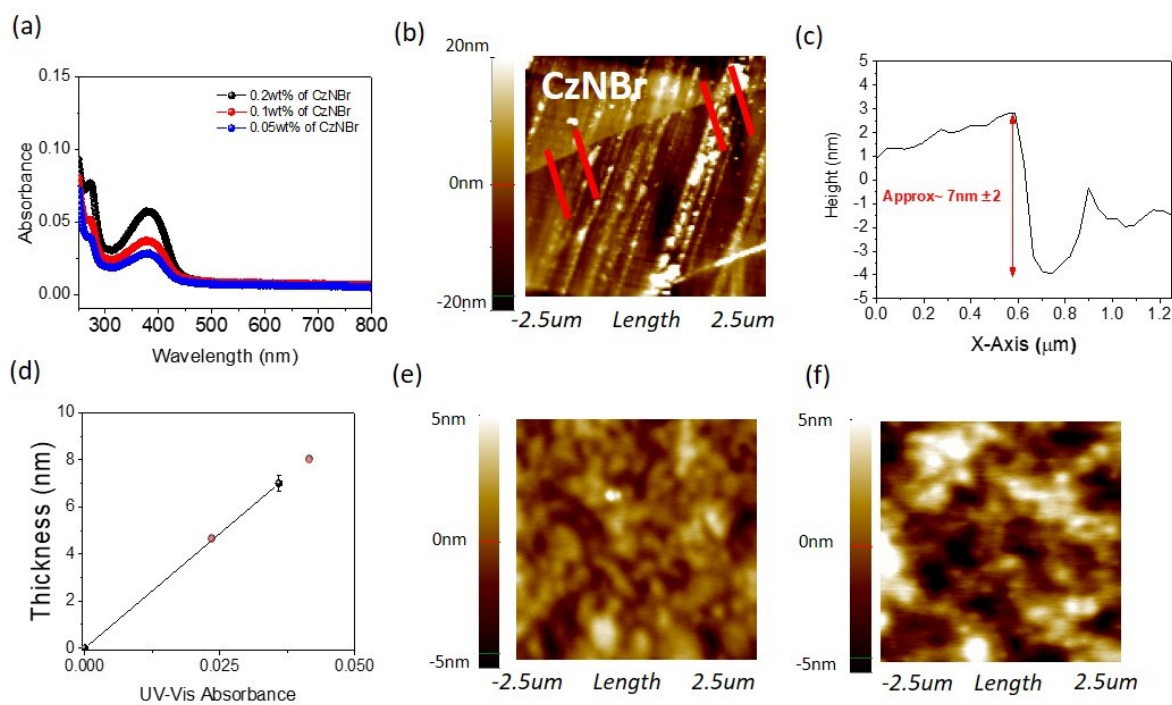


Fig. S8 - (a) UV-Vis spectra of 0.2, 0.1 and 0.05 wt% CzNBr layers deposited on a quartz substrate. (b) AFM images of 0.1 wt% CzNBr deposited on the ITO substrate. (c) The height profiles are measured along the red lines in the corresponding images of (b). (d) shows the estimation of film thickness corresponding to the UV-Vis absorbance of CzNBr according to Beer-lambert's law. (e) and (f) AFM images of the surface morphology corresponding to the structures ITO/PTAA/PFN-Br/MAPbI₃/PC₆₁BM and ITO/PTAA/PFN-Br/MAPbI₃/PC₆₁BM/CzNBr.

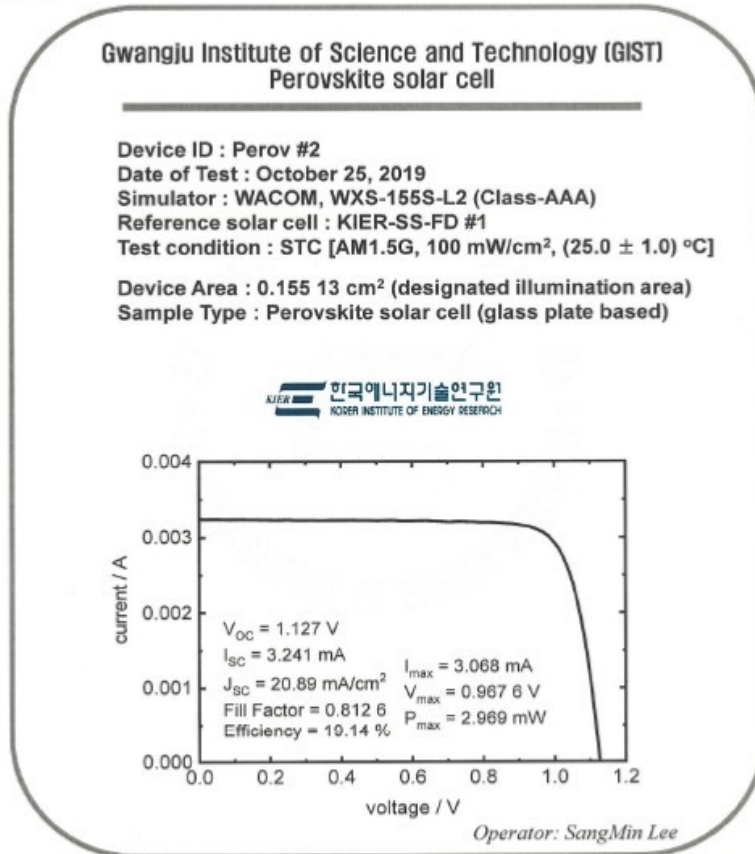


Test Results

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[Appendix 1]



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Fig. S9 - Certificated *J-V* characteristics and photovoltaic parameters of CzNBr devices from the Korea Institute of Energy Research (active area of 0.155 cm²).

	Sweep Direction	J_{sc} (mA/cm ²)	Integrated J_{sc} (mA/cm ²)
w/o CzNBr	FWD	20.75	20.20
	REV	20.67	20.20
w/ CzNBr	FWD	22.70	21.64
	REV	22.78	21.64

Table S1. Summary of J_{sc} values obtained from the J - V curve and integrated J_{sc} values from EQE spectra.

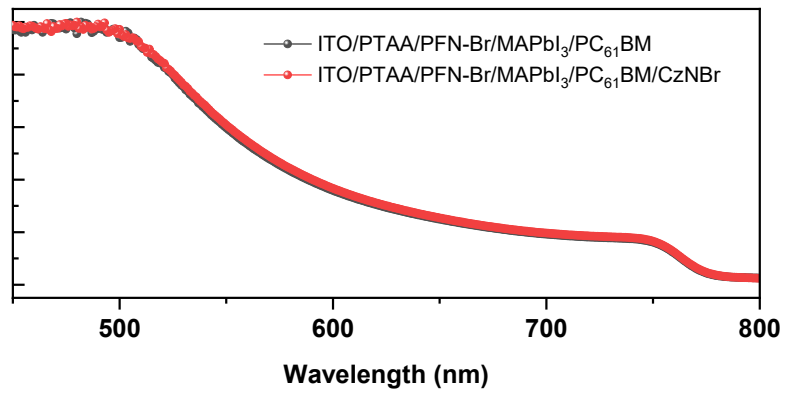


Fig. S10 - (a) UV-Vis spectra of ITO/PTAA/PFN-Br/MAPbI₃/PC₆₁BM and ITO/PTAA/PFN-Br/MAPbI₃/PC₆₁BM/CzNBr.

Table S2. The reported device performance based on pure MAPbI₃ with no additives engineering with n-i-p and p-i-n structure.

Device Structure	Metal Electrode	Charge Transport Layer	Hysteresis	J _{sc} (mA/cm ²)	V _{oc} (V)	FF	PCE (%)	ref
N-I-P	Ag	TiO ₂ /NMTTF	Yes	22.9	1.09	76.5	19.5	1
	Au	SnO ₂ :Eu ³⁺	Yes	22.57	1.06	77.7	20.1	2
	Au	Lanthanum (La)-doped BaSnO ₃	Yes	23.4	1.12	81.3	21.2	3
	Au	c-TiO ₂ /Li-doped m-TiO ₂	Yes	21.46	1.05	81.1	18.3	4
	Au	SnO ₂	No	22.81	1.07	77.6	18.94	5
P-I-N	Cu	Vacuum processed C60/BCP	Yes (Single Crystal)	23.68	1.14	0.81	21.9	6
	Ag	Vacuum processed /BCP/Bi	No	21.62	1.10	0.76	18.02	7
	Al	Solution processed PC ₆₁ BM(Graphdiyne)ZnO	-	23.3	1.02	78.4	20%	8
	Ag	Solution processed TBAOH-SnO ₂	No	21.6	1.08	80.5	18.77	9
	Cu	Solution processed PC ₆₁ BM/BCP	No	21.45	1.09	0.79	18.35	10
	Cu	Vacuum processed C ₆₀ /BCP	No	22.3	1.07	79	19.1	11
P-I-N	Cu	Solution processed PC ₆₁ BM/CzNBr	No	22.78	1.15	0.80	20.3	Our Work

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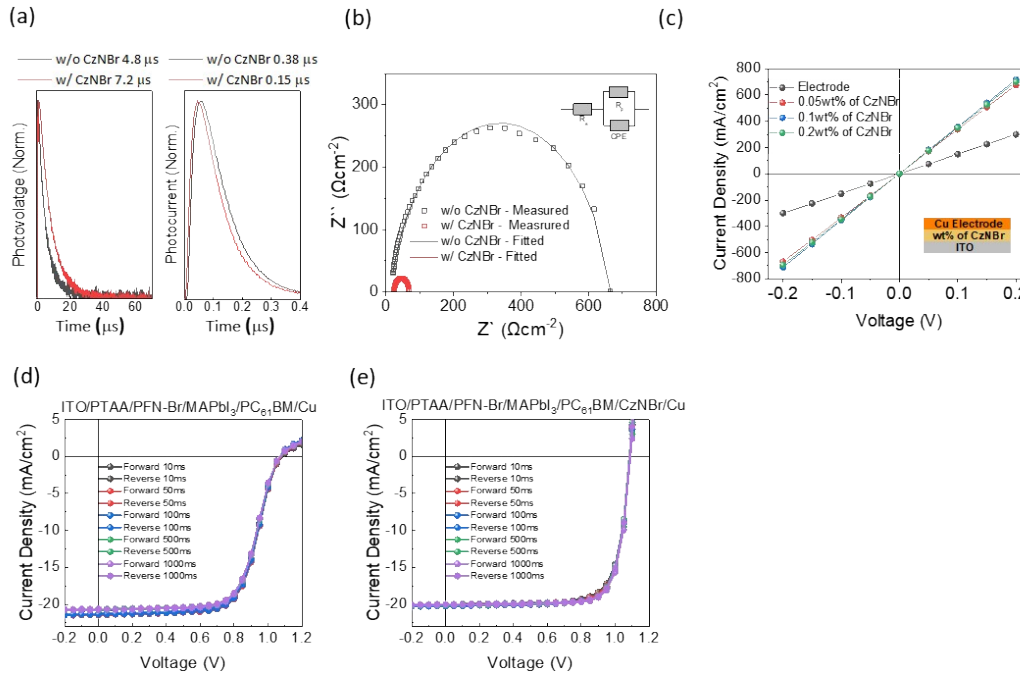


Fig. S11 - (a) Normalized transient photovoltage (TPV, left) and transient photocurrent (TPC, right) decay curves for the I-PSCs with and without CzNBr. (b) Electrochemical impedance spectroscopy (EIS) for I-PSCs with and without CzNBr. Nyquist plots for both devices obtained from the EIS measurement under open-circuit conditions with constant photoirradiation (1 sun, $100 \text{ mW}/\text{cm}^2$), and the inset shows the fitting of the EIS curve to an equivalent circuit model. (c) Series resistance of J-V curves of the Cu electrode and ITO/0.05, 0.1, and 0.2 wt% of CzNBr/Cu. J-V curves for the I-PSC device (d) without and (e) with CzNBr under different scan rates from 10 to 1000 ms.

Table S3. Electrochemical impedance spectroscopy (EIS) measurement fitted parameters for the control and CzNBr devices

	R_p (Ωcm^{-2})	R_s (Ωcm^{-2})	CPE.
w/o CzNBr	651.40	13.33	0.883
w/ CzNBr	45.14	23.50	0.990

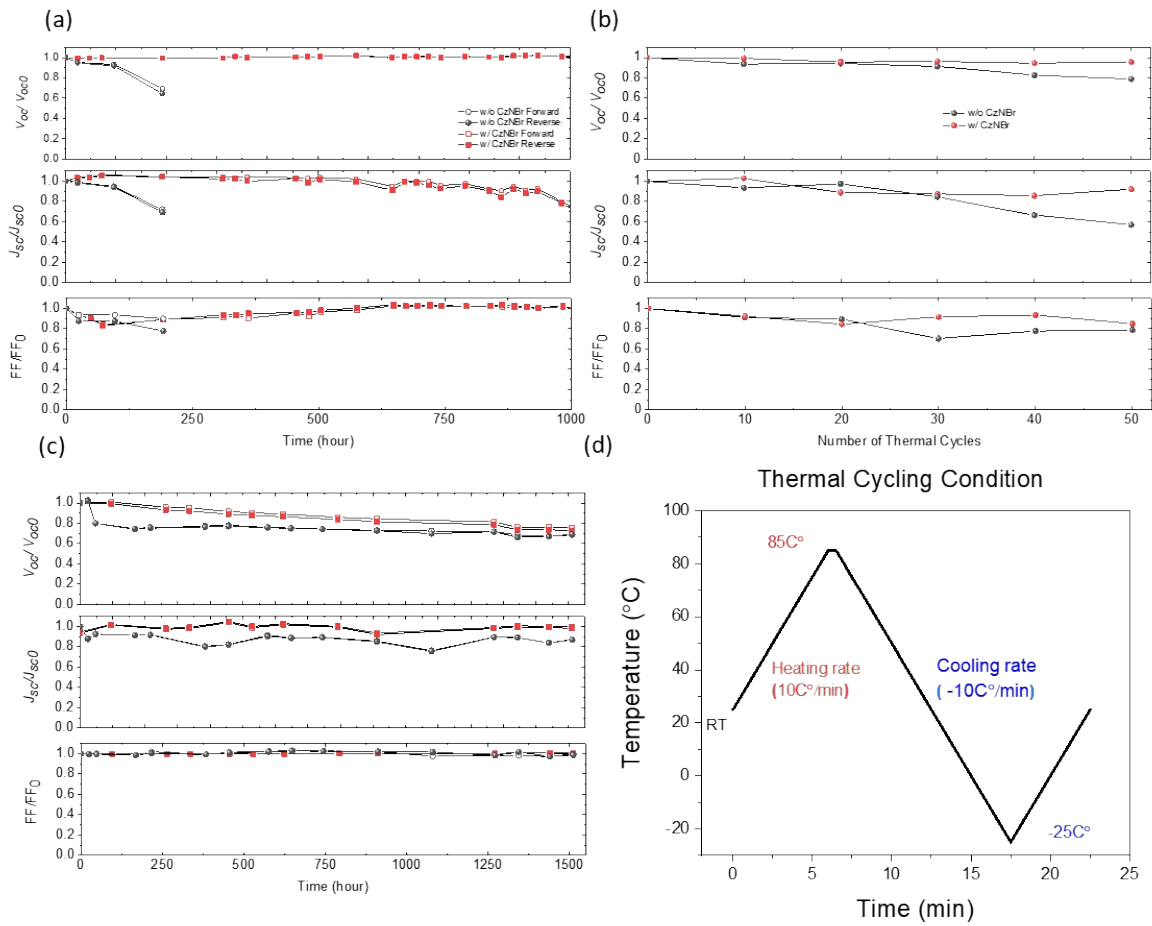


Fig. S12 - Other photovoltaic parameters of the operational stability test of the control and CzNBr device. (a) PCE variations of the control and CzNBr device under continuous thermal annealing at 85°C for 1000 hours under a nitrogen gas atmosphere. (b) PCE variation obtained from the J - V characteristics of the control and CzNBr device after a thermal cycling test of 50 cycles at temperatures between -25°C and 85°C (PCE obtained every 10 cycles in ambient air conditions). (c) Environmental stability performance of the control and CzNBr device under ambient conditions (20-40% relative humidity, $T = 25^\circ\text{C}$) and (d) thermal cycling test conditions for one cycle under high vacuum.

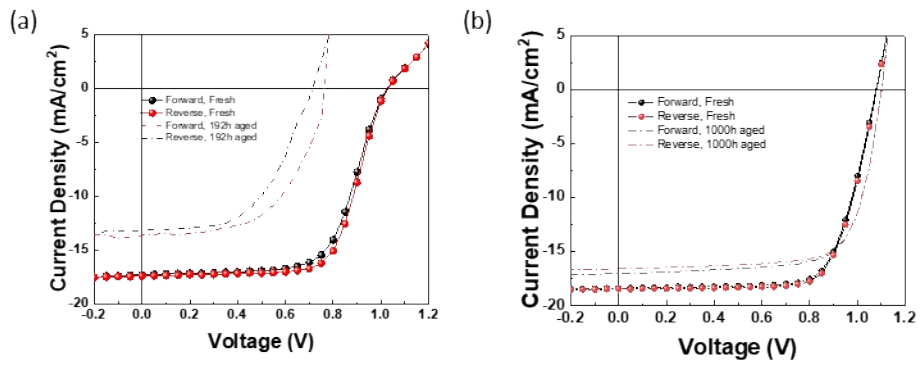


Fig. S13 - *J-V* curves for the cases of as-cast and thermally annealed (a) control and (b) CzNBr devices.

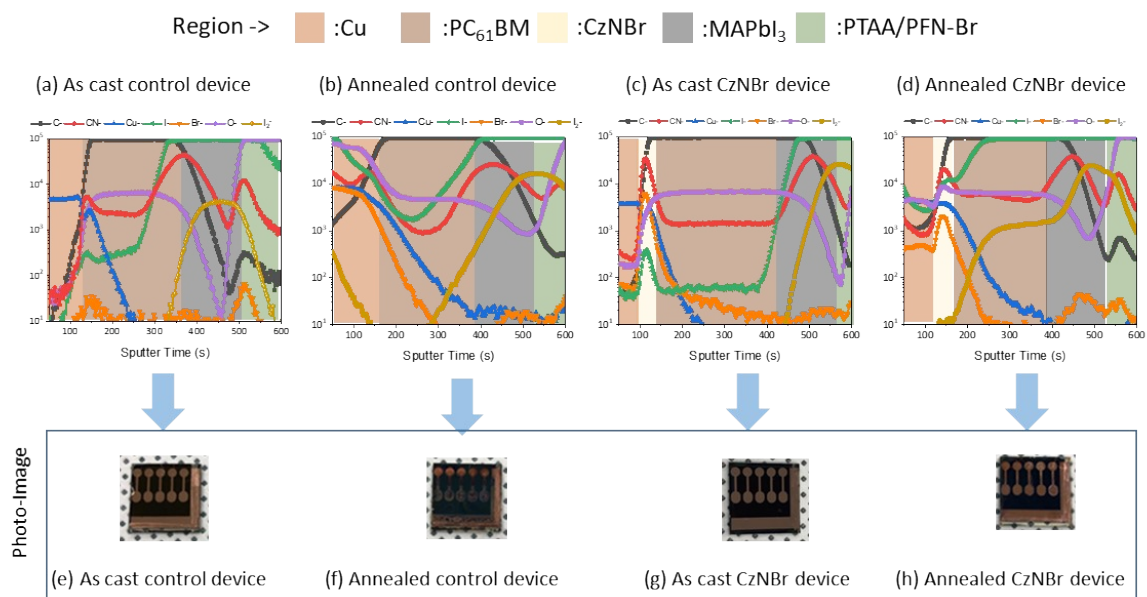


Fig. S14 - ToF-SIMS depth profiles throughout the as-cast and thermally annealed control and CzNBr device. Photographs taken for the control and CzNBr devices before and after 500 h of thermal annealing at 85°C in a N₂-filled glove box. (a), (e) As-cast control device, (b), (f) thermally annealed control device, (c), (g) as-cast CzNBr device and (d), (h) thermally annealed CzNBr device.

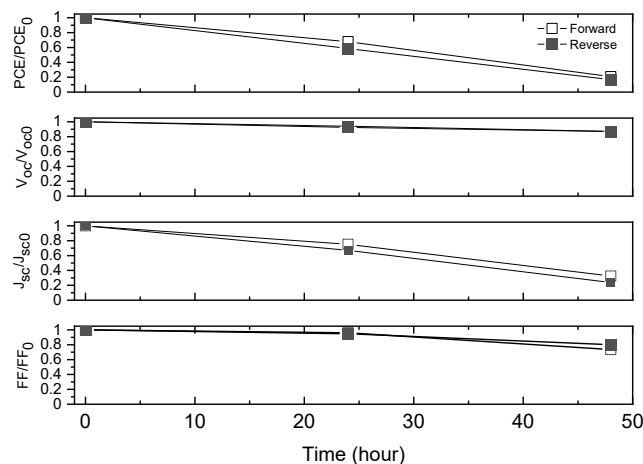


Fig. S15 - The thermal stability test of BCP based device (ITO/PTAA/PFN-Br/MAPBI₃/PC₆₁BM/BCP/Cu) under continuous thermal annealing at 85°C for 50 hours under a nitrogen gas atmosphere

We tested PSC with BCP layer, which is typically used as cathode buffer layer rather than ion scavenging layer in the inverted PSCs. The only function of BCP layer is a modification of the WF of metal electrode to reduce the interfacial barrier at the interface for effectively charge carrier transport. Therefore, BCP based device exhibited relatively poor thermal stability compared to CzNBr based device.

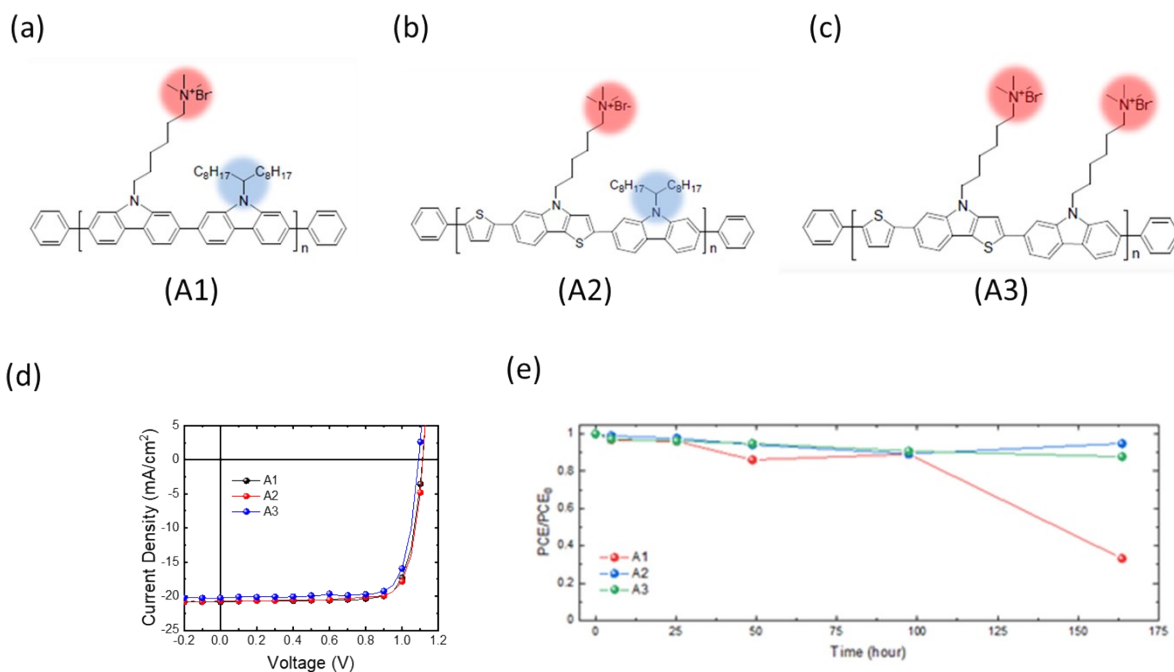


Fig. S16 - (a)-(c) other CPEs (d) J-V curve of PSCs with other CPEs (A1, A2, and A3) (ITO/PTAA/PFN-Br/MAPBI₃/PC₆₁BM/A1, A2 or A3/Cu) and (e) The thermal stability test under continuous thermal annealing at 85°C for 150 hours under a nitrogen gas atmosphere

Photovoltaic performance of PSCs with other CPEs, which have similar chemical structures with CzNBr (A1, A2, and A3), are compared. Thermal stability test for these devices are also tested. However, the best result was obtained with CzNBr layer.

Table S4. Summary of photovoltaic parameter corresponding to the J - V curve of Fig. S16

	Sweep Direction	V_{oc} (V)	J_{sc} (mA/cm²)	FF (%)	PCE(%)
A1	Forward	1.111	20.82	0.79	18.29
A2	Forward	1.113	20.65	0.80	18.32
A3	Forward	1.090	20.23	0.79	17.43

Device Structure	Perovskite Layer	CTL	Fabrication method for CTL	PCE (%)	Degradation Factors			Ref	
					Heat (85°C)	Light	Moisture (air)		
ITO/PTAA/perovskite/C ₆₀ /BCP/Cu	CsFAMAPbI	C ₆₀ /BCP/	Vacuum deposition	22.3	1000h in N ₂ *	MPP ^o	1000h in N ₂ *	-	1
FTO/NiO/perovskite/PCBM/BCP/Cr(Cr ₂ O ₃)/Au	CsFAMAPbI	Cr (Cr ₂ O ₃)	Vacuum deposition	19.8	-	Light soaking (76mWcm ⁻²)	1800h in air*	-	2
ITO/PEDOT:PSS/perovskite/C ₆₀ /BCP/Ag	CsSnFAPbI	C ₆₀ /BCP	Vacuum deposition	16.6	1000h in air*	MPP, Sulphur lamp 0.8 sun	1000h in N ₂ *	-	3
ITO/PTAA/perovskite/pasivation/C ₆₀ /BCP/Cu	FAMAPbIBr	C ₆₀ /BCP	Room temperature [∇] + Vacuum deposition	21	-	MPP	25h	35 days	4
ITO/NiO ₂ /perovskite/ZnO/Al	MAPbI ₃	NiOx	Heat at 300°C for 60min [∇]	16.1	-	-	-	60 days	5
ITO/PTAA/perovskite/PCBM/TiOx/Ag	MAPbI ₃	TiOx	Heat at 100°C for 5min [∇]	16.09	-	MPP	11h in N ₂	200h	6
IT ² PEDOT:PSS/perovskite/PC ₇₁ BM/Ca/Al	MAPbI ₃	Ca/Al	Vacuum deposition	20.1	-	MPP	500s in N ₂	30 days*	7
ITO/PTAA/perovskite/PCBM/TiOx/Cu	MAPbI ₃	TiOx	Vacuum Processing for 100hours	18.8	1000h in N ₂	MPP	1000h in N ₂	-	8
FTO/NiO/perovskite/PCBM/Ag	MAPbI ₃	NiOx	Heat at 500°C for 30min	19.19	500h	Light soaking ^o	1000h in N ₂ *	-	9
ITO/PTAA/perovskite/PCBM/C ₆₀ /BCP/Cu	MAPbI ₃	C ₆₀ /BCP	Vacuum deposition	21.1	-	-	-	940h	10
ITO/PTAA/perovskite/PCBM/CzNBr/Cu	MAPbI ₃	CzNBr	Room temperature [∇]	20.28	1000h in N ₂ (50 cycles for thermal cycling test)	MPP	350h in N ₂	1500h	In this work

Fig. S17 - Summary of state-of-the-art selected I-PSCs, including PCE and various long-term operational stabilities. Only I-PSCs retaining 80% of their initial PCE are included. For photostability, the illumination source of the xenon lamp was used during measurement unless stated otherwise.

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